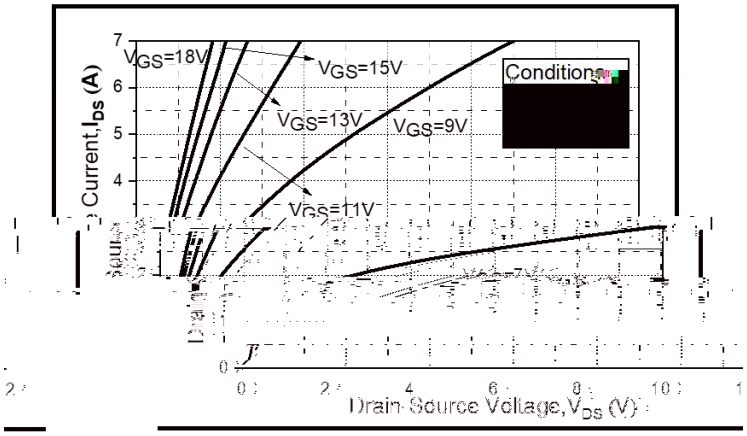
V_{DS}	=	650	V
$R_{DS(on)}$	=	300	mΩ
I_D@25	=	10	A

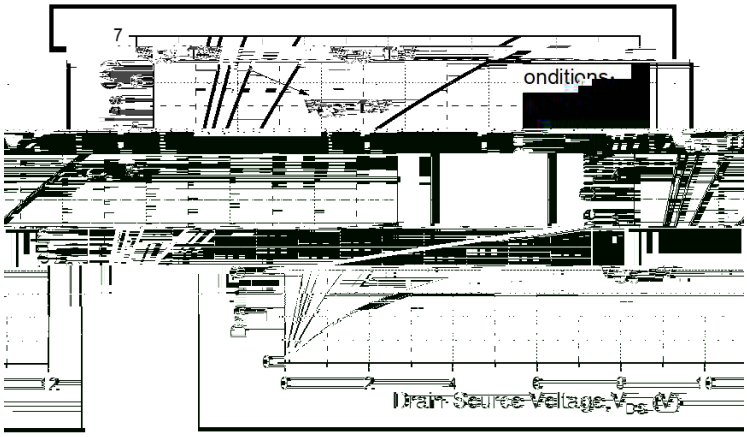
$6)(7

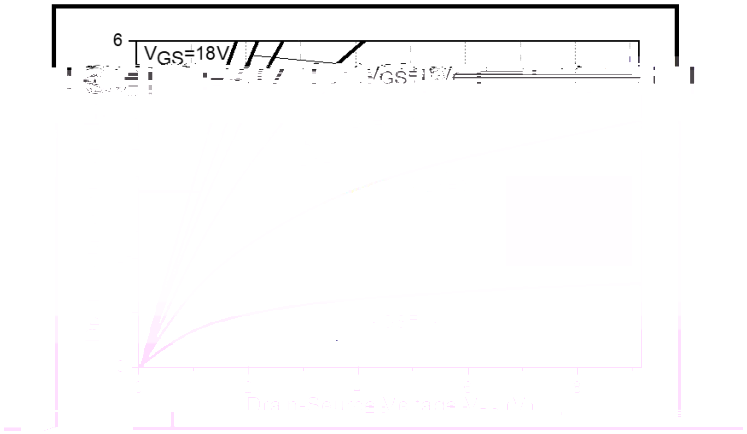
[illegible]

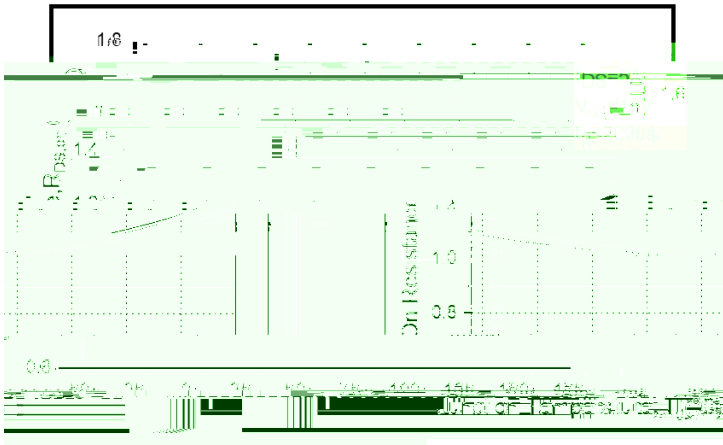
[illegible]

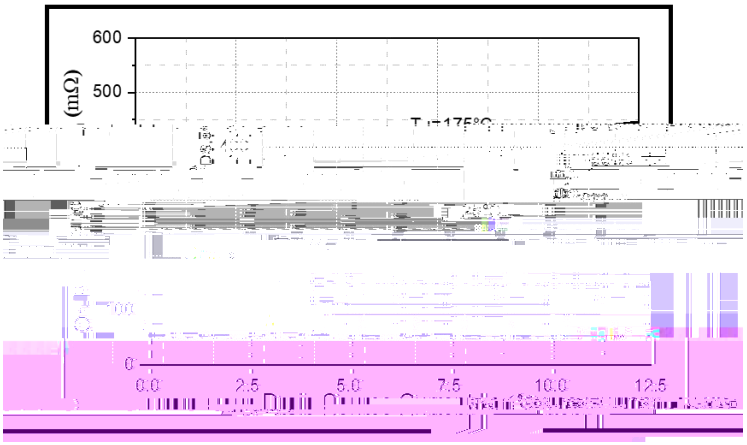
[illegible]

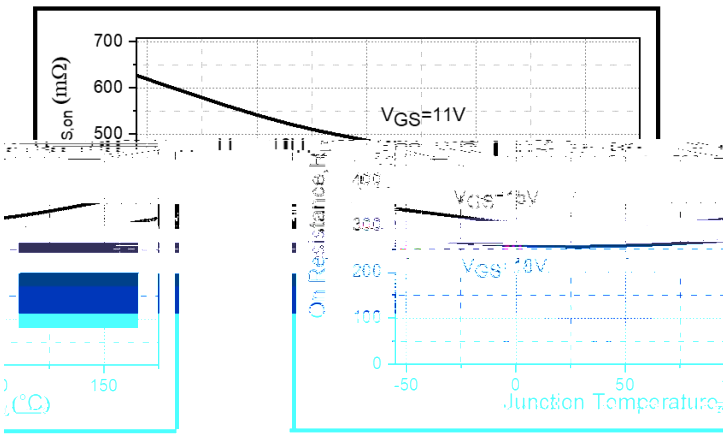

VGS=18V
VGS=15V
VGS=13V
VGS=9V
VGS=11V
Conditions:
Drain Current,IDS (A)
Drain-Source Voltage,VDS (V)

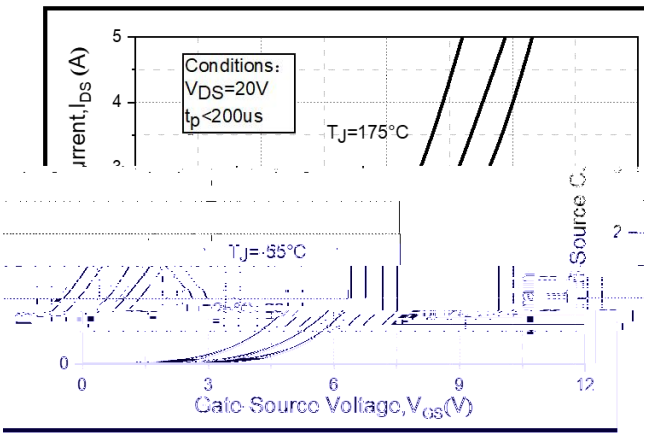

Conditions:
Drain-Source Voltage,VDS (V)

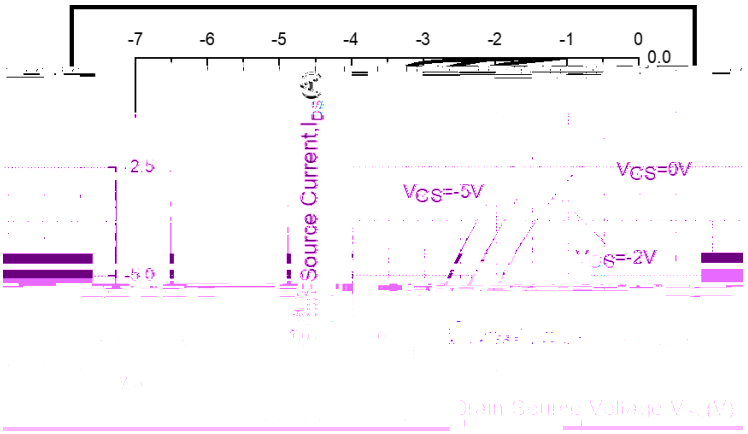

VGS=18V

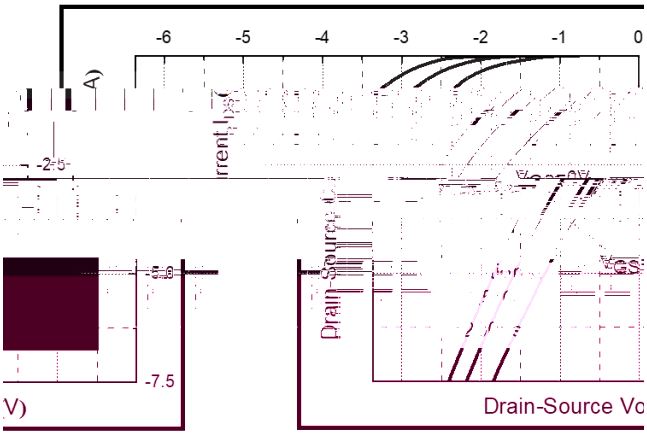


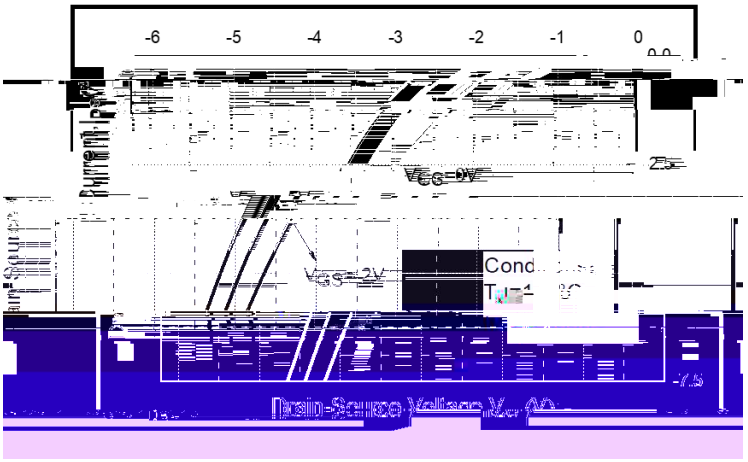

600
500
(mΩ)

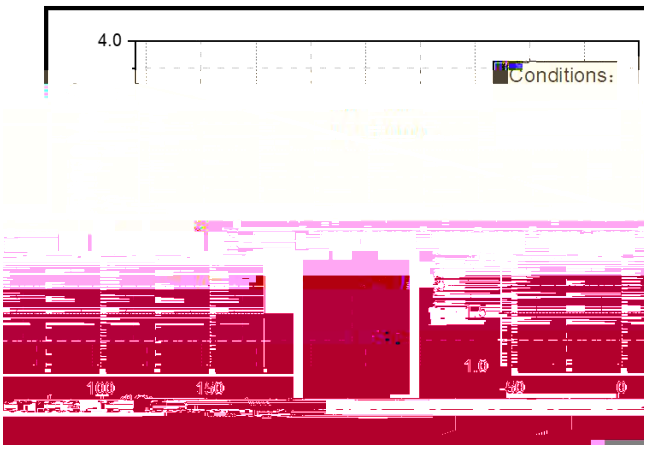

700
600
500
VGS=11V
On Resistance,RDS(on) (mΩ)
Junction Temperature

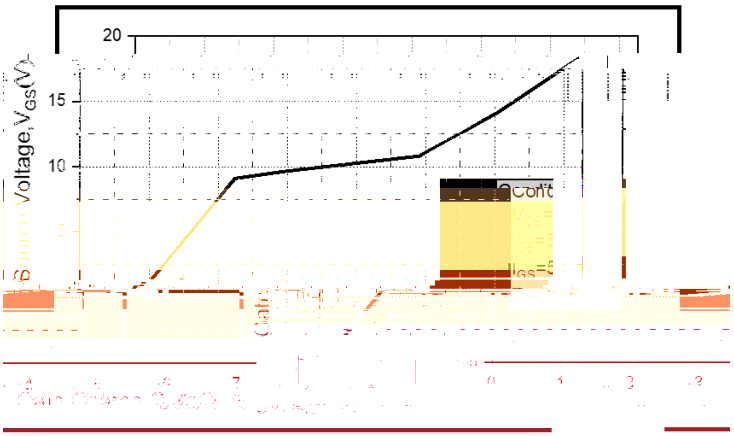

Conditions:
VDS=20V
tp<200us
TJ=175°C
TJ=-55°C
Gate-Source Voltage,VGS(V)

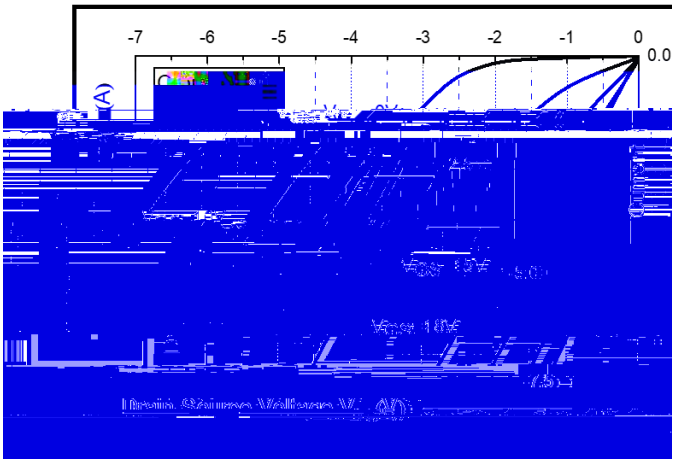

VGS=0V
VGS=-5V
VGS=-2V

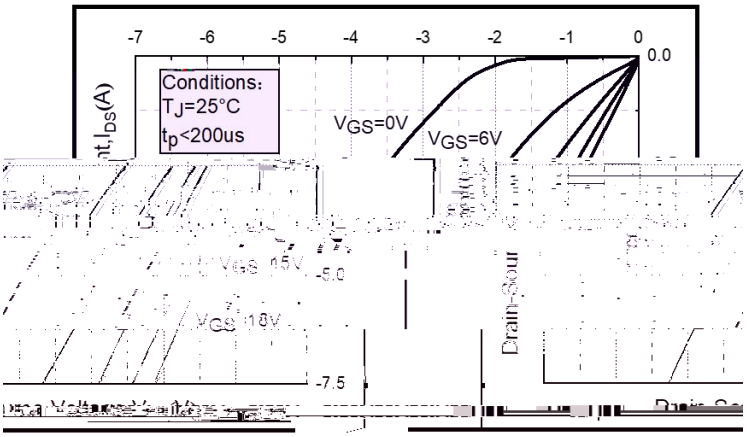

Drain-Source Vo

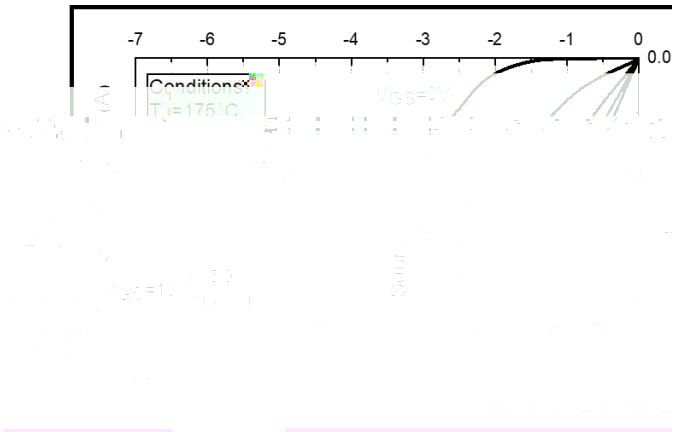

VGS=0V
VGS=-2V
Drain-Source Voltage,VDS(V)

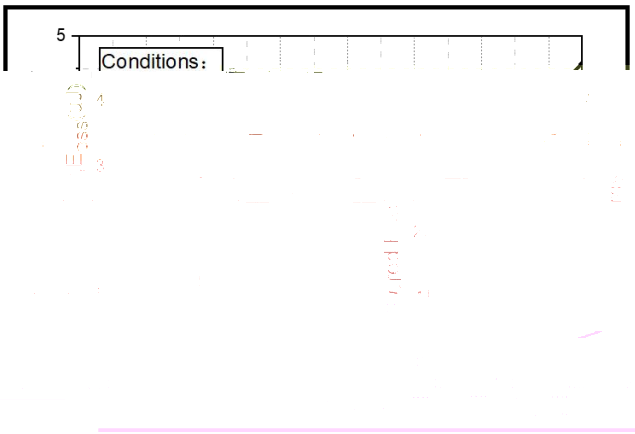

Conditions:

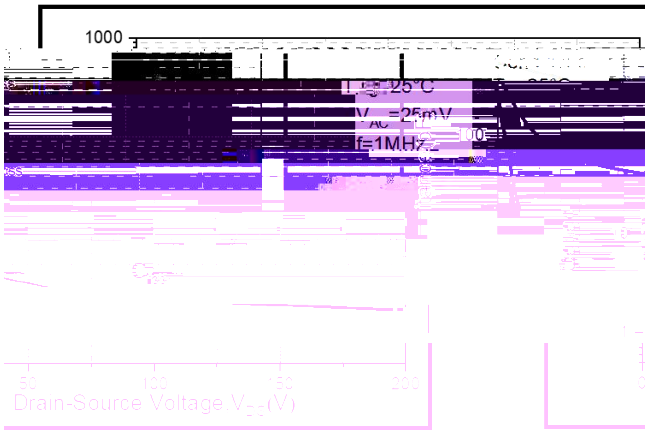

Gate-Source Voltage,VGS(V)

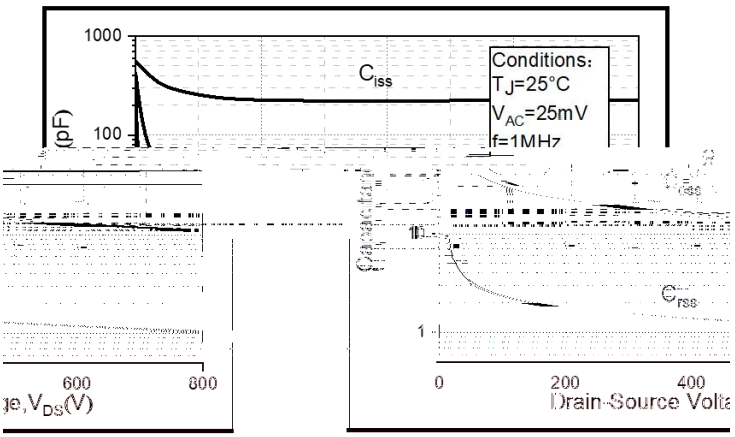

-7
-6
-5
-4
-3
-2
-1
0
0.0

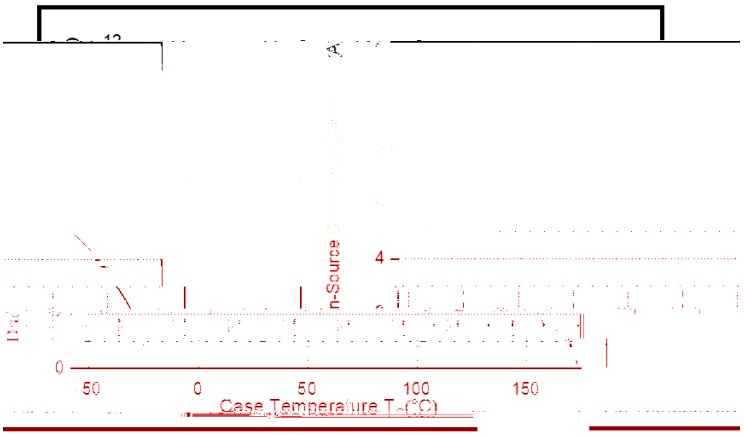

-7
-6
-5
-4
-3
-2
-1
0
0.0
Conditions:
T_J=25°C
t_p<200us
V_{GS}=0V
V_{GS}=6V
V_{GS} 15V
V_{GS} 18V
-5.0
-7.5
Drain-Sour

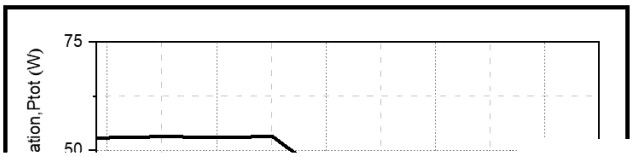

-7
-6
-5
-4
-3
-2
-1
0
0.0
Conditions:
T_J=175°C

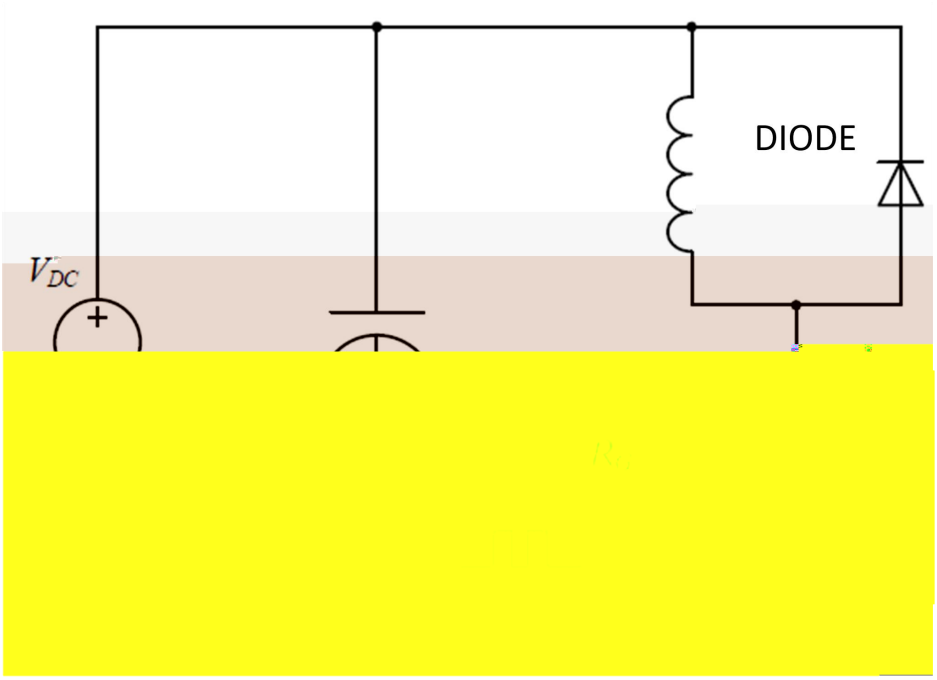

5
Conditions:


1000
T_J=25°C
V_{AC}=25mV
f=1MHz
Drain-Source Voltage V_{DS}(V)


1000
100
(pF)
C_{iss}
Conditions:
T_J=25°C
V_{AC}=25mV
f=1MHz
C_{rss}
1
600
800
V_{DS}(V)
0
200
400
Drain-Source Volta


n-Source
4
0
50
0
50
100
150
Case Temperature T_C (°C)


ation,Ptot (W)
75
50


DIODE
V_{DC}

1) Before using our products, pleamjctpm 'þ

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